Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		@ad<="20020219" and 'SONOS' and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:34
L1	172	@ad<="20020219" and 'ONO' and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 13:57
L3	2	@ad<="20020219" and 'SONOS' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 13:57
L5	1	"20020190311".PN.	US-PGPUB	OR	ON	2004/12/06 14:06
L6	1	"20020142624".PN.	US-PGPUB	OR	ON	2004/12/06 14:06
S1	4	'gate oxide' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/22 07:29
S2	7	@ad<="20020219" and 'ONO' and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 13:55
S3	1	@ad<="20020219" and 'ONO' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 08:28
S4	10	@ad<="20020219" and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 08:32
S5	52	(438/954).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/24 13:24
S6	245	(438/593).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:26
S7	627	(438/770).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:31

S8	481	(438/264).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:27
S9	208	(438/594).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:27
S10	518	(438/275).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 15:32
S11	323	(438/199).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:28
S12	91	(438/477).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:28
S13	77	(438/216).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:28
S14	577	(438/287).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:29
S15	166	(438/783).ccls. and @ad<="20020119"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/24 13:29
S16	8	'gate oxide' and 'in-situ steam generation' or 'LP-RTP'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 10:36
S17	2	("5324675").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/16 10:11
S18	1	'thin film transistor' and 'gate oxide' and 'in-situ steam generation' or 'LP-RTP'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 10:49

S19	27216	@ad<="20020219" and 'TFT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 10:35
S20	226	((@ad<="20020219" and 'TFT') and 'floating gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 10:39
S21	169	((@ad<="20020219" and 'TFT') and 'oxide' and 'floating gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 10:55
S22	1	'tft' and 'in-situ steam generation' or 'LP-RTP'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 11:12
S23	64	((@ad<="20020219" and 'TFT') and 'oxide layer' and 'floating gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 11:04
S24	571	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/16 11:05
S25	11	@ad<="20020214" and (438/149).ccls. and 'floating gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/16 11:06
S26	3585	((438/294) or (438/954) or (438/593-594) or (438/770) or (438/264) or (438/275) or (438/199) or (438/477) or (438/216) or (438/287) or (438/783)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/17 09:50
S27	15	@ad<="20020219" and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 11:57
S28	29	@ad<="20020219" and 'ONO' and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 12:54

S29	27	@ad<="20020219" and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 12:07
S30	2	@ad<="20020219" and 'low pressure rapid thermal process'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 12:17
S31	416	@ad<="20020219" and 'TFT' and 'ONO'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/27 07:12
S32	71	@ad<="20020219" and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/22 08:16
S33	2	("6525384").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/22 09:48
S34	2	"20030155582"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 09:45
S35	2	'TFT' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 10:04
S36	2	("5700699").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/23 09:59
S37	1	'TFT' and 'free radical enhanced rapid thermal oxidation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 10:32
S38	131	@ad<="20020219" and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:25

S39	120	@ad<="20020219" and 'SONOS' same 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:14
S40	1	@ad<="20020219" and 'SONOS device' same 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 12:30
S41	1	@ad<="20020219" and 'SONOS device' same 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 12:31
S42	121	@ad<="20020219" and 'thin film transistor' same 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:16
S43	120	@ad<="20020219" and 'TFT' and 'in-situ steam generation' or 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:17
S44	1	@ad<="20020219" and 'TFT' and ('in-situ steam generation' or 'ISSG')	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:17
S45	37	@ad<="20020219" and 'SONOS device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:18
S46	2	@ad<="20020219" and 'SONOS device' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:18
S47	1	"6319775".PN.	USPAT	OR	OFF	2004/05/27 13:19
S48	1	"6309927".PN.	USPAT	OR	OFF	2004/05/27 13:22
S49	1	"6309927".PN.	USPAT	OR	OFF	2004/05/27 13:23
S50	1	"6248628".PN.	USPAT	OR	OFF	2004/05/27 13:23
S51	1	"6171900".PN.	USPAT	OR	OFF	2004/05/27 13:25
S52	1	@ad<="20020219" and 'in-situ steam generation' same 'SONOS' with 'device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:26

S53	1	@ad<="20020219" and 'in-situ steam generation' same 'SONOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:26
S54	3	@ad<="20020219" and 'SONOS' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:26
S55	2	@ad<="20020219" and 'SONOS' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:27
S56	1	@ad<="20020219" and 'TFT' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:27
S57	39777	@ad<="20020219" and 'Thin film transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:29
S58	13	'SONOS' same 'device' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:44
S59	14	'SONOS' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:45
S60	3	'SONOS' and 'ISSG' with 'process'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:45
S61	2	'TFT' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:45
S62	2	'TFT' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/27 13:45
S63	238	@ad<="20020219" and 'bottom gate TFT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:07

S64	1	@ad<="20020219" and 'tunnel oxide' same 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 06:45
S65	43	@ad<="20020219" and 'oxide' same 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 06:53
S66	4	@ad<="20020219" and 'oxide' same 'ISSG' same 'nitric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 06:47
S67	33	@ad<="20020219" and 'oxide' with 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 06:53
S68	8	@ad<="20020219" and 'silicon oxide' with 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 06:54
S69	7	@ad<="20020219" and 'silicon dioxide' with 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 06:54
S70	0	@ad<="20020219" and 'bottom gate TFT' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:08
S71	80	@ad<="20020219" and 'bottom gate TFT' and 'ISSG' or 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:09
S72	0	@ad<="20020219" and 'bottom gate TFT' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:09
S73	0	@ad<="20020219" and 'bottom gate TFT' and 'RTO'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:10
S74	11	@ad<="20020219" and 'TFT' and 'RTO'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:10

S75	1	@ad<="20020219" and 'TFT' and 'ISSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:10
S76	1	@ad<="20020219" and 'TFT' and 'in-situ steam generation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/30 07:10
S77	3	"6642573"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/25 13:56
S78	2	("5723355").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/25 13:57
S79	2	("5291048").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/25 13:58
S80	2	("6198144").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/25 14:01
S81	2	("5808348").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/25 14:04
S82	2	"20030057475"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/25 14:04